## 2SC4265

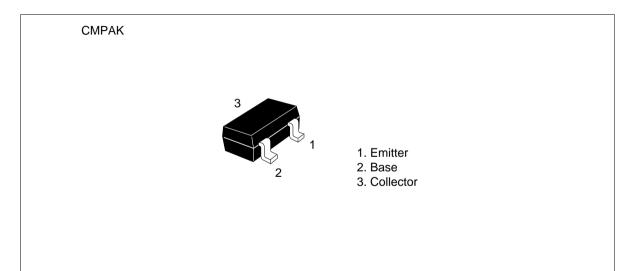
Silicon NPN Epitaxial

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#### Application

VHF RF amplifier, Local oscillator, Mixer

#### Outline





#### 2SC4265

#### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	30	V
Collector to emitter voltage	V <sub>CEO</sub>	20	V
Emitter to base voltage	V <sub>EBO</sub>	3	V
Collector current	Ι <sub>c</sub>	50	mA
Collector power dissipation	Pc	100	mW
Junction temperature	Тј	150	°C
Storage temperature	Tstg	-55 to +150	°C

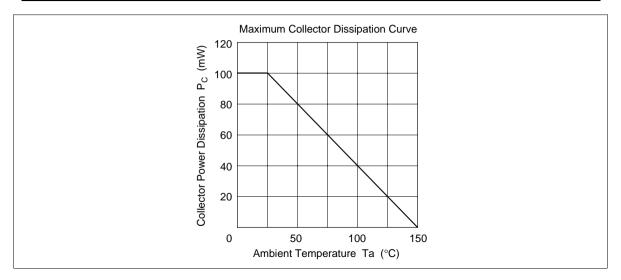
#### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	30	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	20	—	—	V	$I_c = 1 \text{ mA}, R_{BE} = \infty$
Collector cutoff current	I <sub>CBO</sub>	_	_	0.5	μΑ	$V_{ce} = 15 \text{ V}, I_{e} = 0$
Emitter cutoff current	I <sub>EBO</sub>	_		10	μΑ	$V_{EB} = 3 V, I_{C} = 0$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1.0	V	$I_{c} = 20 \text{ mA}, I_{B} = 4 \text{ mA}$
DC current transfer ratio	h <sub>FE</sub>	40	_	_		$V_{ce} = 10 \text{ V}, I_c = 10 \text{ mA}$
Collector output capacitance	Cob	_	_	1.5	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$
Gain bandwidth product	f <sub>T</sub>	600	_	_	MHz	$V_{ce} = 10 \text{ V}, I_c = 10 \text{ mA}$
Noto: Marking is "IC"						

Note: Marking is "JC".

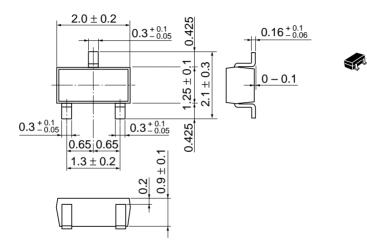
See characteristic curves of 2SC2735.

### 2SC4265



#### HITACHI

Unit: mm



Hitachi Code	CMPAK
JEDEC	
EIAJ	Conforms
Weight (reference value)	0.006 g

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